

### Is Now Part of



# ON Semiconductor®

# To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to Fairchild <a href="guestions@onsemi.com">guestions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



### FDS6930B

# Dual N-Channel Logic Level PowerTrench® MOSFET

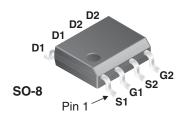
### **Features**

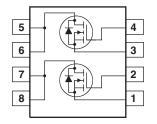
- 5.5 A, 30 V.  $R_{DS(ON)} = 38 \text{ m}\Omega$  @  $V_{GS} = 10 \text{ V}$   $R_{DS(ON)} = 50 \text{ m}\Omega$  @  $V_{GS} = 4.5 \text{ V}$
- Fast switching speed
- Low gate charge
- High performance trench technology for extremely low R<sub>DS(ON)</sub>
- High power and current handling capability

### **General Description**

These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.





### Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V <sub>DSS</sub>	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage	± 20	V	
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	5.5	А
	- Pulsed	İ	20	
$P_{D}$	Power Dissipation for Dual Operation (Note 1)		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1	
		(Note 1c)	0.9	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to 150	°C
Thermal Cha	aracteristics	•		
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)		78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

### **Package Marking and Ordering Information**

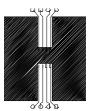
Device Marking	Device	Reel Size	Tape width	Quantity
FDS6930B	FDS6930B	13"	12mm	2500 units

## **Electrical Characteristics** $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Charac	teristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		26		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			1 10	μА
I <sub>GSS</sub>	Gate-Source Leakage	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA
On Charact	teristics (Note 2)	•	•	•	•	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.9	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		-4.6		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}$ $V_{GS} = 4.5 \text{ V}, I_D = 4.8 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 5.5 \text{ A}, T_J = 125 ^{\circ}\text{C}$		31 40 45	38 50 62	mΩ
I <sub>D(on)</sub>	On-State Drain Current	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 5 V	20			Α
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 5.5 A		19		S
Dynamic C	haracteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		310	412	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		90	120	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			40	60	pF
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 15 mV, f = 1.0 MHz		1.9		Ω
Switching (	Characteristics (Note 2)	•	-	•		
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 1 A,		6	12	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		6	12	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			16	28	ns
t <sub>f</sub>	Turn-Off Fall Time			2	4	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 5.5 A,		2.7	3.8	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 5 V		1.0		nC
Q <sub>gd</sub>	Gate-Drain Charge			0.7		nC
Drain-Sour	rce Diode Characteristics and Maximun	n Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				1.3	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.3 A (Note 2)		0.8	1.2	V
t <sub>rr</sub>	Diode Reverse Recovery Time (note3)	$I_F = 5.5 \text{ A}, d_{iF}/d_t = 100 \text{ A/}\mu\text{s}$		16	32	nS
Q <sub>rr</sub>	Diode Reverse Recovery Charge			6		nC

#### Notes:

R<sub>BJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>BJC</sub> is guaranteed by design while R<sub>BCA</sub> is determined by the user's board design.



a) 78°C/W when mounted on a 0.5 in<sup>2</sup> pad of 2 oz



b) 125°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2 oz copper



c) 135°C/W when mounted on a minimum pad.



Scale 1:1 on letter size paper

- 2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%
- 3. Trr parameter will not be subjected to 100% production testing.

### **Typical Characteristics**

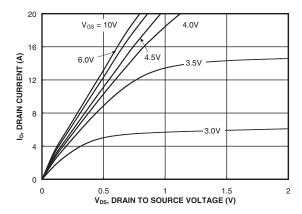


Figure 1. On-Region Characteristics.

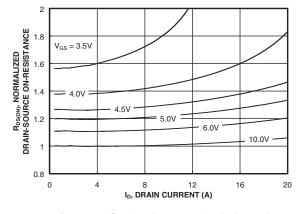


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

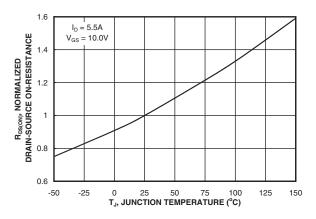


Figure 3. On-Resistance Variation with Temperature.

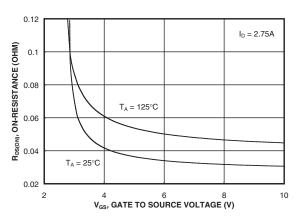


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

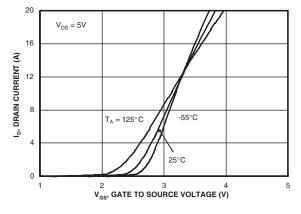


Figure 5. Transfer Characteristics.

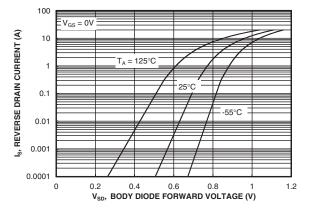
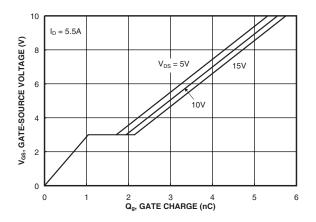


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

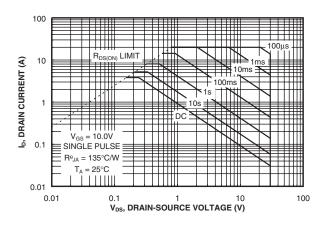
### **Typical Characteristics**



 $\begin{array}{c} \textbf{500} \\ \textbf{400} \\ \textbf{400} \\ \textbf{200} \\ \textbf{C}_{\text{ISS}} \\ \textbf{C}_{\text{SSS}} \\ \textbf{C}_{\text{SSS}} \\ \textbf{V}_{\textbf{DS}}, \textbf{DRAIN TO SOURCE VOLTAGE (V)} \\ \end{array}$ 

Figure 7. Gate Charge Characteristics.





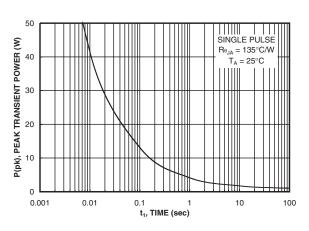


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

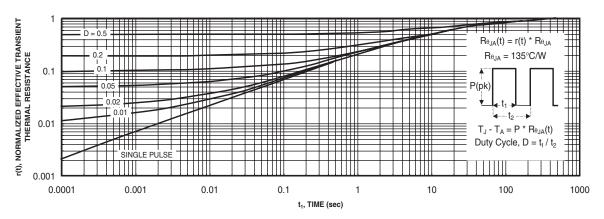


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.





#### **TRADEMARKS**

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

 $\begin{array}{lll} \mathsf{AccuPower^{\mathsf{TM}}} & \mathsf{F-PFS^{\mathsf{TM}}} \\ \mathsf{Auto-SPM^{\mathsf{TM}}} & \mathsf{FRFET}^{\$} \\ \end{array}$ 

Build it Now<sup>TM</sup> Global Power Resource<sup>SM</sup>

CorePLUS™ Green FPS™

CorePOWER<sup>TM</sup> Green FPS<sup>TM</sup> e-Series<sup>TM</sup>  $CROSSVOLT^{TM}$   $Gmax^{TM}$ 

CTL™ GMaX™
CTL™ GTO™
Current Transfer Logic™ IntelliMAX™
DEUXPEED® ISOPLANAR™
Dual Cool™ MegaBuck™
EcoSPARK® MICROCOUPLER™
EfficientMax™ MicroFET™
ESBC™ MicroPak™

Fairchild® MillerDrive™ MillerDrive™ MotionMax™ Motion-SPM™ OptoHiT™ OPTOLOGIC® FAST® OPTOPLANAR®

FastvCore™ FETBench™ FlashWriter<sup>®</sup>\*

FlashWriter PDP SPM<sup>TM</sup>

Power-SPM™ PowerTrench® PowerXS™

Programmable Active Droop™

QFET<sup>®</sup>
QS<sup>™</sup>
Quiet Series<sup>™</sup>
RapidConfigure<sup>™</sup>

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™ SPM®

SPM
STEALTH™
SUPERSOT™-3
SUPERSOT™-6
SUPERSOT™-8
SUPERSOT™-8
SUPERMOS™
SyncFET™
Sync-Lock™

The Power Franchise® the power Franchise Franchise TinyBoost™
TinyBoost™
TinyCalc™
TinyCalc™
TinyPOTOTM
TinyPOWer™
TinyPOWer™
TinyPWM™
TinyWire™
TriFault Detect™
TRUECURRENT™\*
µSerDes™

SerDes
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
XS™

\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

#### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

#### As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### **ANTI-COUNTERFEITING POLICY**

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Definition of Terms				
Datasheet Identification	Product Status	Definition		
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.		
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.		
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.		
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.		

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdt/Patent-Marking.pdf">www.onsemi.com/site/pdt/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

### **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D TPCC8103,L1Q(CM MIC4420CM-TR VN1206L SBVS138LT1G 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C BUK954R8-60E NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE222 NTE2384 NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956 NTE2956 NTE2911 DMN2080UCB4-7 TK10A80W,S4X(S SSM6P69NU,LF DMP22D4UFO-7B